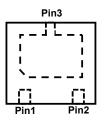


PTVSHC3N10VU

Uni-directional 10V High Capacitance TVS

Description

The PTVSHC3N10VU Transient Voltage Suppressor is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The PTVSHC3N10VU protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. The PTVSHC3N10VU is available in a DFN2×2-3L package with working voltages of 10 volt.





Feature

- 4000W Peak pulse power per line (t_P = 8/20µs)
- DFN2×2-3L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD)
 ±30kV(air), ±30kV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

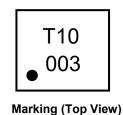
Applications

- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C

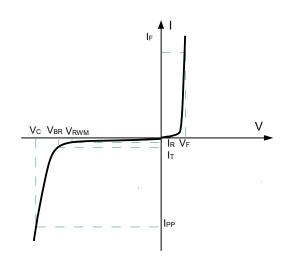
Pin 1, 20 Pin 3 Circuit Diagram



PTVSHC3N10VU

Electronics Parameter

Symbol	Parameter	
V _{RWM}	Peak Reverse Working Voltage	
IR	Reverse Leakage Current @ VRWM	
V _{BR}	Breakdown Voltage @ I⊤	
Iτ	Test Current	
IPP	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
P _{PP}	Peak Pulse Power	
CJ	Junction Capacitance	
IF	Forward Current	
VF	Forward Voltage @ I _F	



Electrical characteristics per line@25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Peak Reverse Working Voltage	VRWM				10	V
Breakdown Voltage	V _{BR}	I⊤=1mA	11	12	13.5	V
Reverse Leakage Current	I _R	V _{RWM} =10V			1	μA
Clamping Voltage	Vc	I _{PP} =20A t _P = 8/20µs		12.5	14	V
Clamping Voltage	Vc	I _{PP} =140A t _P = 8/20µs		17.5	19.5	V
Clamping Voltage	Vc	I _{PP} =200A t _P = 8/20µs		20	22	V
Junction Capacitance	CJ	V _R =0V f = 1MHz		1300	1500	pF

Notes : Measured from pin 3 to pin 1 and pin 2.

Absolute maximum rating@25°C

Rating	Symbol	Value	Unit
Peak Pulse Power(t _P = 8/20µs)	P _{pp}	4000	W
Peak Pulse Current (t⊵ = 8/20µs)	Ірр	200	A
Lead Soldering Temperature	ΤL	260 (10 sec)	°C
Operating Temperature	TJ	-55 to 150	°C
Storage Temperature	Тѕтс	-55 to 150 °C	

PTVSHC3N10VU

Typical Characteristics

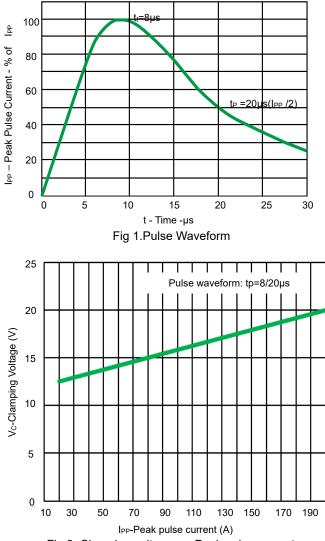
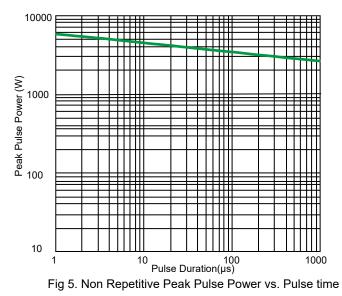
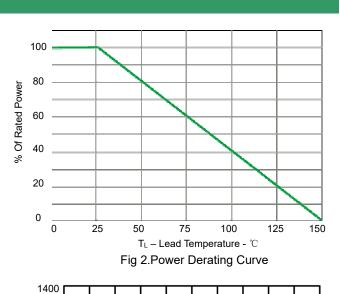
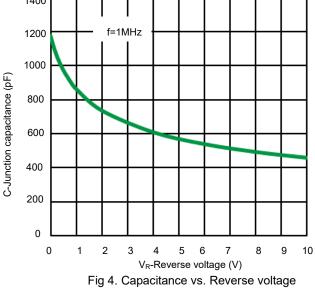


Fig 3. Clamping voltage vs. Peak pulse current

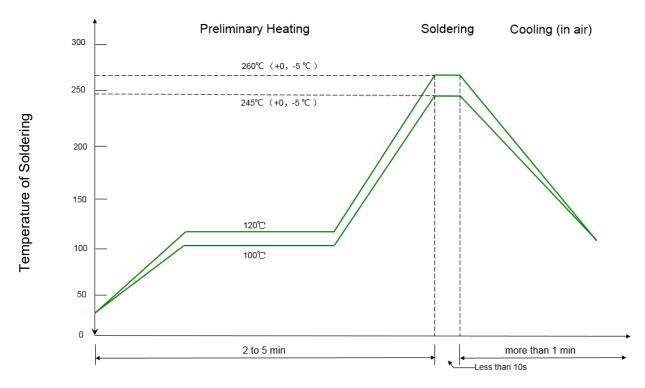






PTVSHC3N10VU

Solder Reflow Recommendation



Remark: Pb free for 260°C; Pb for 245°C.

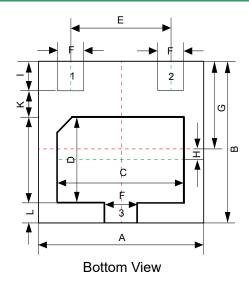
PCB Design

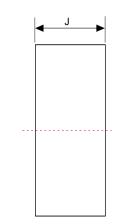
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- > Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

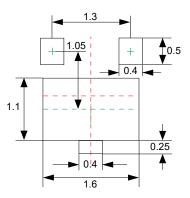
PTVSHC3N10VU

Product dimension (DFN2×2-3L)





Dim	Millimeters		
DIM	MIN	МАХ	
A	1.90	2.10	
В	1.90	2.10	
С	1.40	1.60	
D	0.90	1.15	
E	1.30BSC		
F	0.25	0.40	
G	0.90	1.10	
н	0.20	0.30	
I	0.32	0.48	
J	0.50 0.65		
К	0.20	0.45	
L	0.15 0.30		



Unit:mm

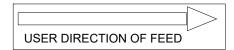
Recommended Soldering Pad

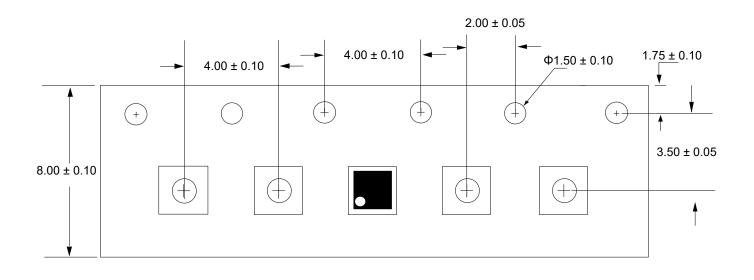
Ordering information

Device	Package	Reel	MPQ
PTVSHC3N10VU	DFN2×2-3L (Pb-Free)	7"	3000 / Tape & Reel

PTVSHC3N10VU

Load with information





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